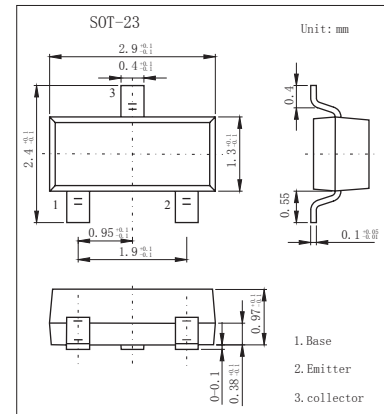


PNP Transistors

2SA733

■ Features

- Collector-Base Voltage: $V_{CB0} = -60V$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-150	mA
Power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = -50 \mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -50 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6 V, I_C = -1 mA$	120		475	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -10 mA$		-0.18	-0.3	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -6 V, I_C = -1.0 mA$	-0.58	-0.62	-0.68	V
Collector output capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0, f = 1 MHz$		4.5	7	pF
Noise figure	NF	$V_{CE} = -6 V, I_C = -0.3 mA, R_g = 10 k\Omega, f = 100 Hz$		6	20	dB
Transition frequency	f_T	$V_{CE} = -6 V, I_C = -10 mA$	50			MHz

■ Marking

Marking	M6	CSL	CSH
Range	200-400	120-220	220-475



炬芯微
XUANXINWEI

SMD Type

Transistors

2SA733

Typical Characteristics

